

Osamu Oda

List of Publications by Year in descending order

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7
papers

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citations

1937685
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7
docs citations

7
times ranked

52
citing authors

#	ARTICLE	IF	CITATIONS
1	Epitaxial growth of GaN by radical-enhanced metalorganic chemical vapor deposition (REMOCVD) in the downflow of a very high frequency (VHF) N ₂ /H ₂ excited plasma – effect of TMG flow rate and VHF power. Journal of Crystal Growth, 2014, 391, 97-103.	1.5	20
2	Effects of Radical Species on Structural and Electronic Properties of Amorphous Carbon Films Deposited by Radical-Injection Plasma-Enhanced Chemical Vapor Deposition. Plasma Processes and Polymers, 2016, 13, 730-736.	3.0	10
3	Novel Epitaxy for Nitride Semiconductors Using Plasma Technology. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, .	1.8	7
4	Growth of InN films by radical-enhanced metal organic chemical vapor deposition at a low temperature of 200 Å°C. Japanese Journal of Applied Physics, 2017, 56, 06HE08.	1.5	4
5	Effect of N ₂ /H ₂ plasma on GaN substrate cleaning for homoepitaxial GaN growth by radical-enhanced metalorganic chemical vapor deposition (REMOCVD). AIP Advances, 2018, 8, 115116.	1.3	4
6	Effects of plasma shield plate design on epitaxial GaN films grown for large-sized wafers in radical-enhanced metalorganic chemical vapor deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 031201.	1.2	4
7	Simulation-aided design of very-high-frequency excited nitrogen plasma confinement using a shield plate. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	1.2	2